



P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on) max}	I _D T _A = +25°C	
201/	8mΩ @ VGs = -10V	-17A	
-30V	10.2mΩ @ V _{GS} = -4.5V	-14.5A	

Description

This new generation MOSFET has been designed to minimize the onstate resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- DC-DC Converters
- Power management functions
- Backlighting

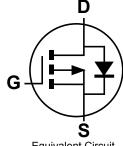
Features and Benefits

- Low Input Capacitance
- Low On-Resistance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Tin Finish annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.33 grams (approximate)







Ordering Information (Note 4 & 5)

Part Number	Compliance	Case	Packaging
DMP3010LK3-13	Standard	TO252	2,500/Tape & Reel
DMP3010LK3Q-13	Automotive	TO252	2,500/Tape & Reel

S

D

D

Top View

Pin-Out

G

1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

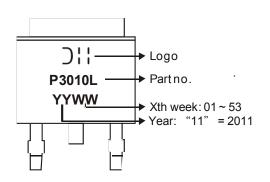
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_grade_definitions/.

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html

Marking Information

Notes:





Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value -30	Units V		
Drain-Source Voltage	V _{DSS}				
Gate-Source Voltage	V _{GSS}	±20	V		
	Steady State	T _A = +25°C T _A = +70°C	ID	-17.0 -13.0	А
Continuous Drain Current (Note 7) V_{GS} = -10V	t<10s	T _A = +25°C T _A = +70°C	ID	-27.0 -21.0	А
	Steady State	T _A = +25°C T _A = +70°C	ID	-14.5 -11.5	А
Continuous Drain Current (Note 7) V _{GS} = -4.5V	t<10s	T _A = +25°C T _A = +70°C	ID	-23.0 -18.0	А
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I _{DM}	-100	А		
Maximum Body Diode Forward Current (Note 7)	ls	5.5	А		
Avalanche Current (Note 8)	I _{AS}	47	А		
Avalanche Energy (Note 8)			E _{AS}	113	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Total Power Dissipation (Note 6)	PD	1.7	W	
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	P	72	°C/W
mermar Resistance, Junction to Ambient (Note 0)	t<10s	$R_{ heta}$ JA	29	°C/W
Total Power Dissipation (Note 7)		PD	3.4	W
Thermal Decistence, Junction to Ambient (Note 7)	Steady state	P	37	°C/W
Thermal Resistance, Junction to Ambient (Note 7)	t<10s	$R_{ extsf{ heta}JA}$	15	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)	Symbol	IVIIII	Тур	WidX	Unit	Test condition	
Drain-Source Breakdown Voltage	BV _{DSS}	-30	_		V	V _{GS} = 0V, I _D = -250µA	
Zero Gate Voltage Drain Current	I _{DSS}		_	-1	μA	$V_{DS} = -30V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)			-				
Gate Threshold Voltage	V _{GS(th)}	-1.1	-1.6	-2.1	V	V _{DS} = V _{GS} , I _D = -250µA	
Static Drain-Source On-Resistance	Р	_	6.5	8	mΩ	V _{GS} = -10V, I _D = -10A	
	R _{DS (ON)}	_	7.2	10.2	11122	$V_{GS} = -4.5V, I_{D} = -10A$	
Forward Transfer Admittance	Y _{fs}	_	30	_	S	V _{DS} = -15V, I _D = -10A	
Diode Forward Voltage	V _{SD}	_	-0.65	-1.0	V	V _{GS} = 0V, I _S = -1A	
DYNAMIC CHARACTERISTICS (Note 10)		_					
Input Capacitance	C _{iss}		6234	_		V _{DS} = 15V, V _{GS} = 0V f = 1.0MHz	
Output Capacitance	C _{oss}	_	1500		pF		
Reverse Transfer Capacitance	C _{rss}	_	774	_			
Gate Resistance	R _G	_	1.28		μ	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz	
Total Gate Charge	Qg	_	59.2	_			
Gate-Source Charge	Q _{gs}	_	16.1		nC	V _{DS} = -15V, V _{GS} = -4.5V, I _D = -10A	
Gate-Drain Charge	Q _{gd}	_	15.7				
Turn-On Delay Time	t _{D(on)}		11.4			V _{DS} = -15V, V _{GEN} = -10V,	
Turn-On Rise Time	tr		9.4				
Turn-Off Delay Time	t _{D(off)}		260.7	_	ns	R _G = 6Ω, I _D = -1A	
Turn-Off Fall Time	t _f		99.3				

Notes: 6. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

7. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

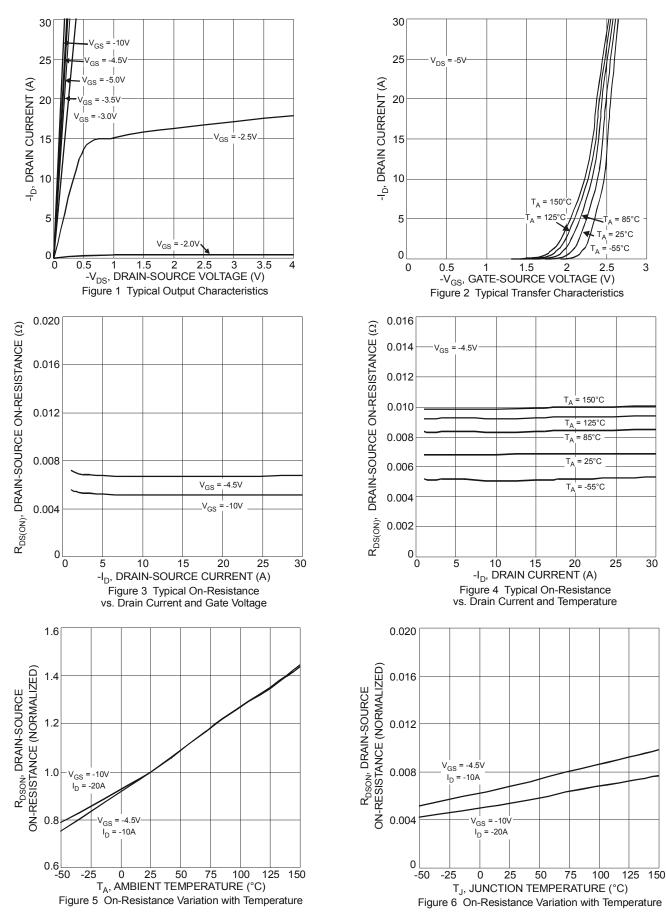
8 .UIS in production with L = 0.1mH, T_J = +25°C.

9. Short duration pulse test used to minimize self-heating effect.

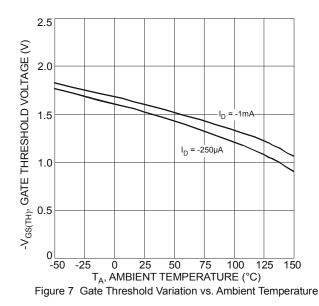
10. Guaranteed by design. Not subject to production testing.

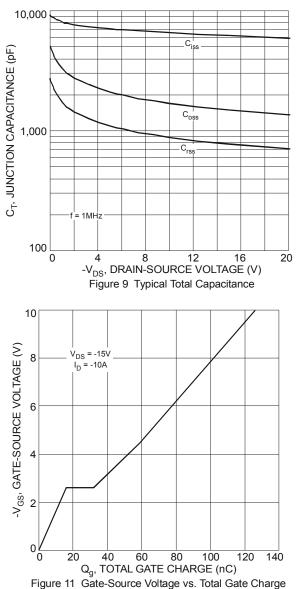
DMP3010LK3

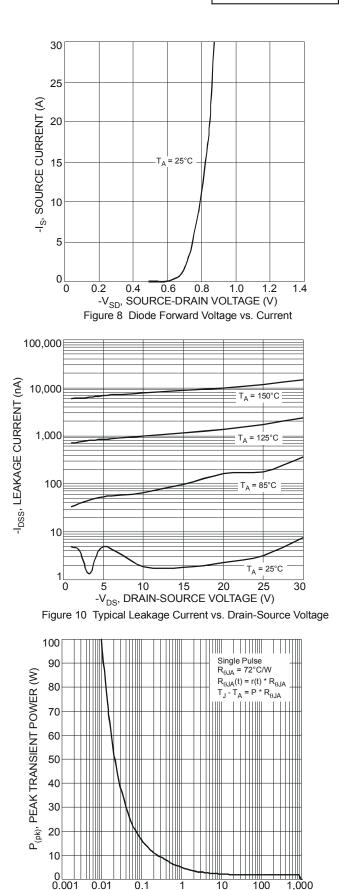












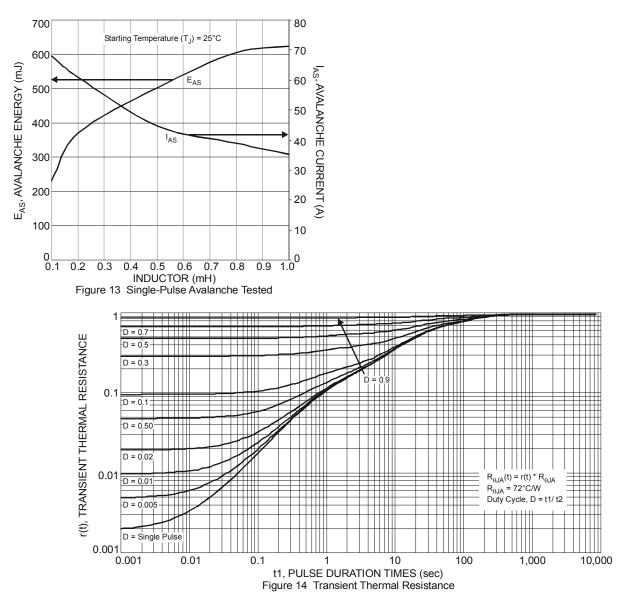
01 0.1 1 10 100 t1, PULSE DURATION TIME (sec) Figure 12 Single Pulse Maximum Power Dissipation

0.01

1,000

100

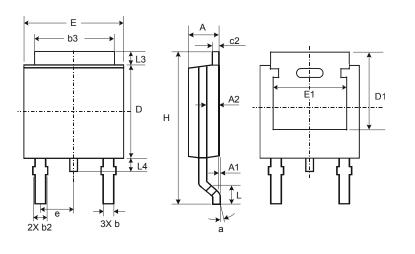






Package Outline Dimensions

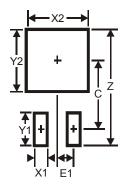
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



	TO252						
Dim	Min	Max	Тур				
Α	2.19	2.39	2.29				
A1	0.00	0.13	0.08				
A2	0.97	1.17	1.07				
b	0.64	0.88	0.783				
b2	0.76	1.14	0.95				
b3	5.21	5.46	5.33				
c2	0.45	0.58	0.531				
D	6.00	6.20	6.10				
D1	5.21	-	-				
е	-	-	2.286				
Е	6.45	6.70	6.58				
E1	4.32	-	-				
Н	9.40	10.41	9.91				
L	1.40	1.78	1.59				
L3	0.88	1.27	1.08				
L4	0.64	1.02	0.83				
а	0°	10°	_				
All	All Dimensions in mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	11.6
X1	1.5
X2	7.0
Y1	2.5
Y2	7.0
C	6.9
E1	2.3



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